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				ate for TPS24710/711/712/713							CN Date.	02/17/2013	
										Quality Services			
Customer Contact: PCN Manager Change Type:			Dept:							Quality Services			
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Texas Instruments Incorporated is announcing an information only notification.													
The product detechant(s) is being undeted as sure resulted below													
The product datasheet(s) is being updated as summarized below.													
The following change history provides further details													
The following change history provides further details													
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TP	S247	10, TPS24711									IN IN	XAS STRUMENTS	
		12, TPS24713											
SL\	SLVSAL2F – JANUARY 2011–REVISED FEBRUARY 2015 www.ti.com									www.ti.com			
Ch	2000	from Pavision E /A	lovember 2012)	to D	ovicion	_						Page	
CII		from Revision E (N										Page	
•	Added ESD Rating table, Feature Description section, Device Functional Modes, Application and Implementation												
	section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section												
	Changed the Input voltage range, PROG - MAX value in the Absolute Maximum Ratings table From: 0.3 To: 3.6												
	Deleted External capacitance - GATE from the Recommended Operating Conditions												
Deleted text from the last paragraph in the GATE section "If used, any capacitor connecting GATE and GND should													
	not exceed 1 μF and it should be connected in series with a resistor of no less than 1 kΩ."												
Deleted section: Alternative Design Example: GATE Capacitor (dV/dt) Control in Inrush Mode													
Deleted text from the High-Gate-Capacitance Applications section "When gate capacitor dV/dt control is used,													
then a Zener diode is not necessary."													
The	data	asheet number	will be chan	aina	٦.								
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The	יכפ כ	hanges may be	reviewed at	the	data	sheet link	s nrov	vided					
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D -		for Character											
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To more accurately reflect device characteristics.													
Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):													
Fle	Flectrical specification performance changes as indicated above												

Changes to product identification resulting from this PCN:							
None.							
Product Affected:							
TPS24710DGS	TPS24711DGS	TPS24712DGS	TPS24713DGS				
TPS24710DGSR	TPS24711DGSR	TPS24712DGSR	TPS24713DGSR				

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

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